Monday, 13 September 2010

5:00 – 7:00 pm Reception

Tuesday, 14 September 2010

8:30 - 8:45 Welcome address

Graphene growth 1 - Chair: Dennis Hess
8:45 – 9:15 Epitaxial graphene on SiC (0001)
Thomas Seyller  University of Erlangen-Nürnberg, Germany

9:15 – 9:45 Structural and electronic properties of epitaxial graphene on SiC (0001): Growth, transfer doping and hydrogen intercalation
Ulrich Starke  Max Planck Institute for Solid State Research, Stuttgart, Germany

9:45 – 10:15 Formation of epitaxial graphene on SiC (0001) - comparison of Si-face and C-face for different annealing environments
Randall Feenstra  Carnegie-Mellon University, Pittsburgh, USA

10:15 - 10:45 Coffee Break

Graphene growth 2 - Chair: Wlodek Strupinski
10:45 – 11:15 Large homogenous graphene layers on SiC (0001) and buffer layer elimination
Leif Johansson  Linköping University, Sweden

11:15 – 11:45 Mastering large area epitaxial graphene on SiC
Rositza Yakimova  Linköping University, Sweden

11:45 – 12:15 Surface electron microscopy of epitaxial graphene
Hiroki Hibino  NTT Basic Research Laboratories, Japan

12:15 - 2:00 Lunch

Electronic structure 1 - Chair: Gérard Martinez
2:00 – 2:30 Electronic structure of epitaxial graphene monolayer: theoretical perspective
Olef Pankratov  University Erlangen-Nürnberg, Germany

2:30 – 3:00 Commensuration and interlayer coherence in twisted bilayer graphenes
Gene Mele  University of Pennsylvania, Philadelphia, USA

3:00 – 3:30 Rotated graphene bilayers from independent layer to electronic localization
Laurence Magaud  CNRS, Grenoble, France

3:30 – 4:00 Coffee Break

Electronic structure 2 – Chair: Michael Williams
4:00 – 4:30 Observation of plasmarons in quasi-freestanding epitaxial graphene
Eli Rotenberg  Lawrence Berkeley National Laboratory, Berkeley, USA

4:30 – 5:00 Exploring the structural and electronic properties of rotated graphene film
Edward Conrad  Georgia Institute of Technology, Atlanta, USA

5:00 – 5:30 Giant anisotropic spin splitting in epitaxial graphene
Klaus Kern  Max Planck Institute, Stuttgart, Germany & EPFL, Lausanne, Switzerland

5:30 - 7:00 Poster session
**Graphene growth 3 – Chair David Snyder**

8:30 – 9:00  **Orientation-mediated control of interfacial structure in epitaxial graphene on silicon substrates**  
Maki Suemitsu  
Tohoku University, Japan

9:00 – 9:30  **Initiating graphene growth and dielectric deposition**  
Kurt Gaskill  
Naval Research Laboratory, Washington, USA

9:30 – 10:00  **Large area and structured epitaxial graphene produced by confinement controlled sublimation of silicon carbide**  
Walt de Heer  
Georgia Institute of Technology, Atlanta, USA

10:00 – 10:20  **Coffee Break**

**Graphene growth 4 & Theory – Chair Dimitri Vvedensky**

10:20 – 10:40  **The role of carbon surface diffusion on the growth of epitaxial graphene on SiC**  
Taisuke Ohta  
Sandia National Labs, Albuquerque, USA

10:40 – 11:00  **Models of the Growth of Epitaxial Graphene**  
Andrew Zangwill  
Georgia Institute of Technology, Atlanta, USA

11:00 – 11:30  **Electronic and optical properties of graphene structures**  
Steven Louie  
University of California, Berkeley, USA

11:30 – 11:50  **Coffee Break**

**Devices 1 – Chair: James Meindl**

11:50 – 12:20  **Progress and challenges of graphene FETs for RF applications**  
Yu-Ming Lin  
IBM Watson Research Center, USA

12:20 – 12:50  **Self-aligned graphene on SiC and Graphene-on-Si MOSFETs on 75mm wafers**  
Jeong-Sun Moon  
Hughes Research Labs, USA

**Afternoon Free**
Transport 1 – Chair: Natalya Goncharuk

8:30 - 9:00 Magic Twist Angles in Layered Graphene
Allan MacDonald  University of Texas, Austin, USA

9:00 – 9:30 Subwavelength devices in graphene
Didier Mayou  CNRS, Grenoble, France

9:30 – 10:00 Electronic and transport properties of graphene systems
Mei-Yin Chou  Georgia Institute of Technology, Atlanta, USA

10:00 – 10:30 Coffee Break

Transport 2 – Chair: Wilfried Poirier

10:30 – 11:00 Transport on gated C-face epitaxial graphene
Claire Berger  CNRS, Grenoble, France and Georgia Tech, Atlanta, USA

11:00 - 11:30 Magneto-transport on epitaxial graphene
Peide Ye  Purdue University, West Lafayette, USA

11:30 – 12:00 Charge transport in epitaxial graphene: magneto-resistance, Quantum Hall effect and gating
Heiko Weber  University of Erlangen-Nürnberg, Germany

12:00 - 1:30 Lunch

Device 2 – Chair: Paul Campbell

1:30 – 2:00 Epitaxial graphene and few layer graphitic growth on SiC and sapphire substrate
Michael Spencer  Cornell University, Ithaca, USA

2:00 – 2:20 Graphene spintronics with high impedance injectors
Bruno Dlubak  CNRS-Thales Group, Palaiseau, France

2:20 – 2:40 Spin transport in few layer graphene
Thomas Maassen  University of Groningen, Netherlands

2:40 – 3:10 Coffee Break

Landau levels imaging – Chair: Ramesh Mani

3:10 – 3:40 Spatial Mapping of Landau Levels in Graphene
Phillip First  Georgia Institute of Technology, Atlanta, USA

3:40 - 4:10 Real-space theory of the interlayer coupling in epitaxial graphene
Markus Kindermann  Georgia Institute of Technology, Atlanta, USA

4:10 – 4:40 Scanning tunneling spectroscopy of fractional Hall physics in epitaxial graphene
Young Jae Song  NIST, Gaithersburg, USA

4:40 – 6:00 Poster session

7:00 Banquet at the Sliders Sea Side Restaurant
2nd International Symposium on the Science and Technology of Epitaxial Graphene

Friday, September 17

Optical properties – Chair: Roman Stępniewski
8:30 - 9:00 Multilayer epitaxial graphene versus graphitic multilayer structures
Marek Potemski CNRS, Grenoble, France
9:00 – 9:30 Ultrafast spectroscopy of epitaxial graphene
Ted Norris University of Michigan, Ann Arbor, USA
9:30 - 9:50 Coffee Break

Graphene growth 5 – Dominique Vignaud
9:50 – 10:20 Structure of the interface between graphene and 6H-SiC(0001) investigated by STM
Jean-Yves Veuillen CNRS, Grenoble, France
10:20 – 10:50 Understanding and monitoring epitaxial graphene/SiC surfaces and interfaces properties
Patrick Soukiassian University of Paris Sud, Orsay & CEA, Saclay, France
10:50 – 11:10 HREELS Investigation of the graphene/silicon carbide interaction
Roland Koch University Erlangen-Nürnberg, Germany
11:10 – 11:30 Coffee Break

Surface functionalization – Chair: Matthew Chisholm
11:30 – 11:50 Superlattice of resonator on monolayer graphene created by intercalated gold nanoclusters
Laurent Simon CNRS, Mulhouse, France
11:50 – 12:20 Graphene: scratching the surface
Michael Fuhrer University of Maryland, College Park, USA
12:20 – 12:50 Advances in graphene chemistry
Robert Haddon University of California, Riverside, USA
12:50 – 13:00 Departure Address